

Fig. 1

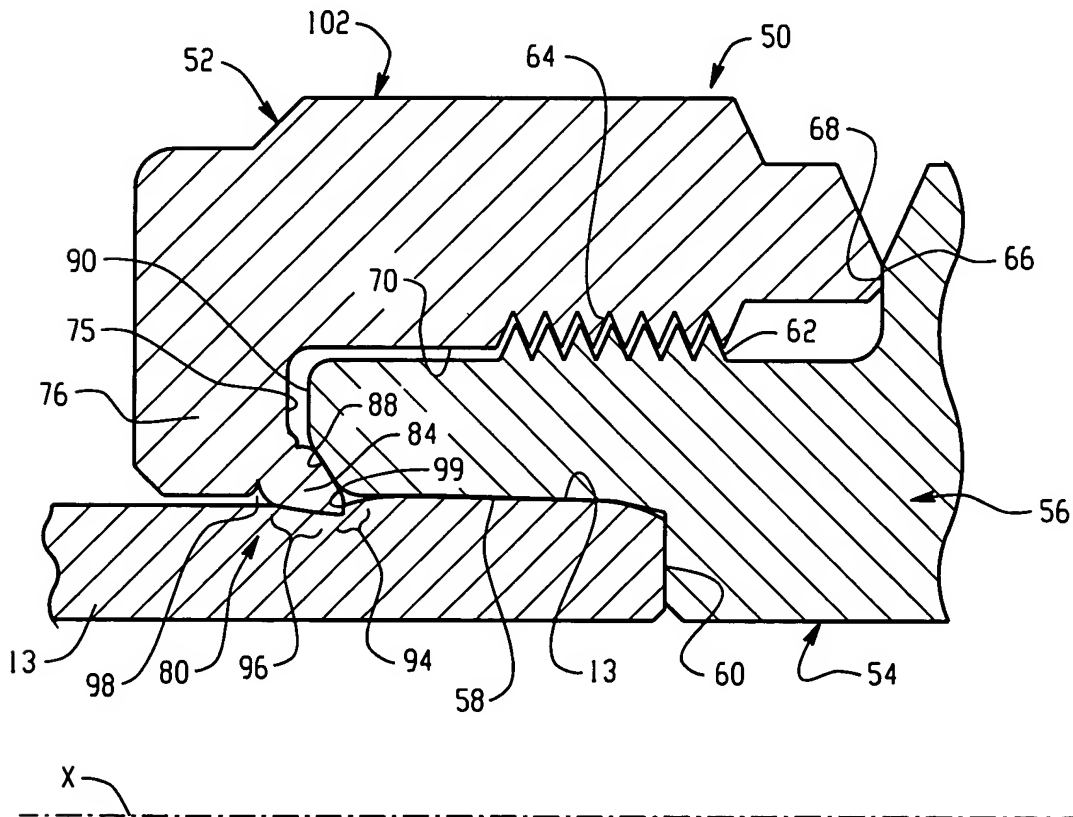


Fig. 2

Fig. 4

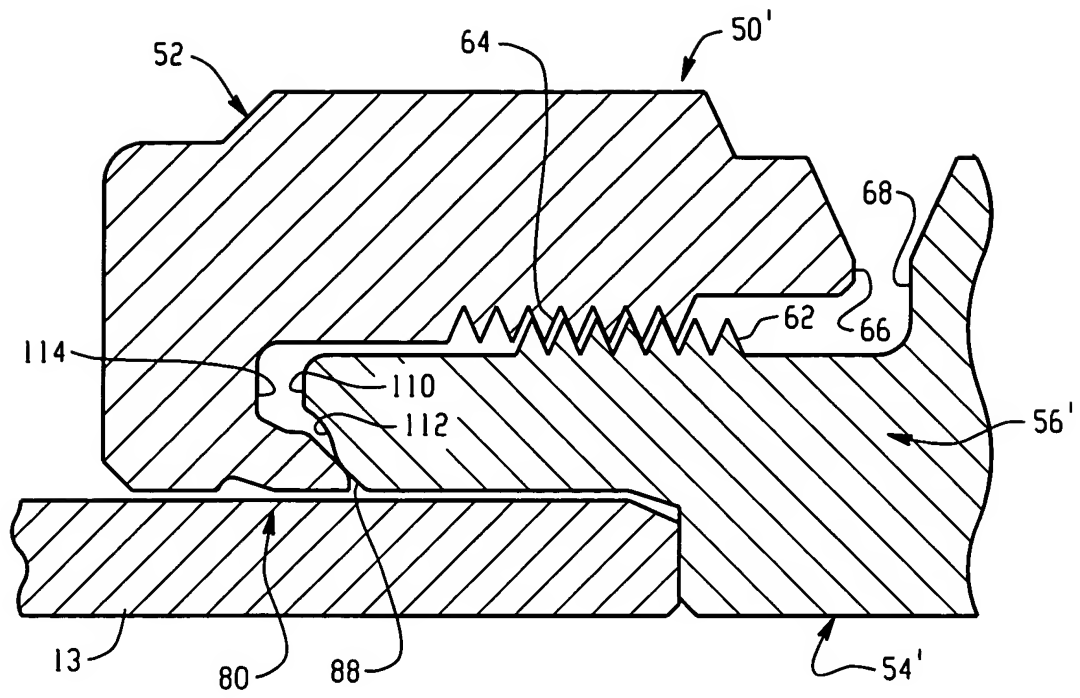


Fig. 5

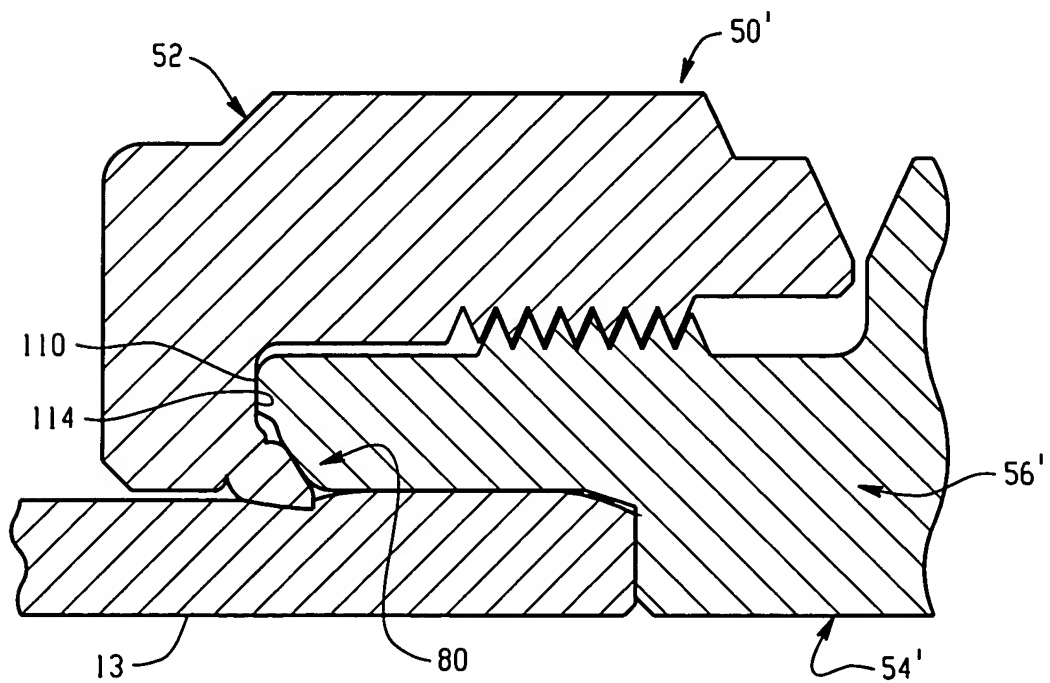
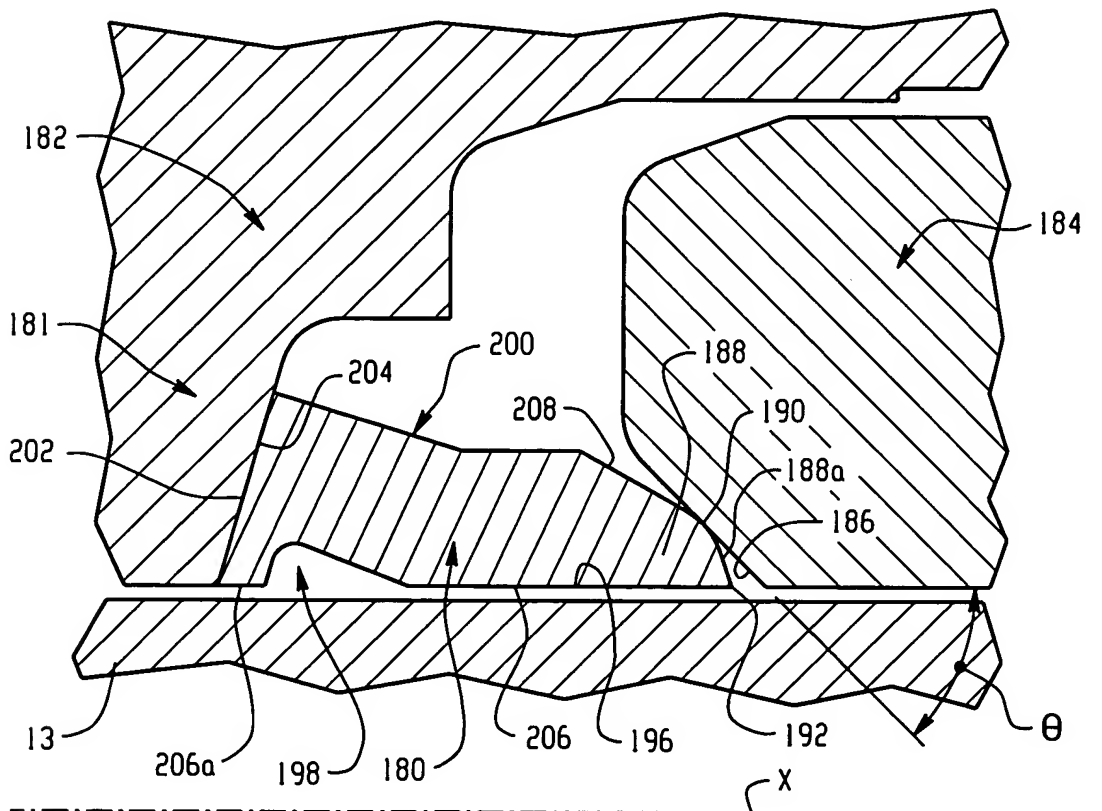
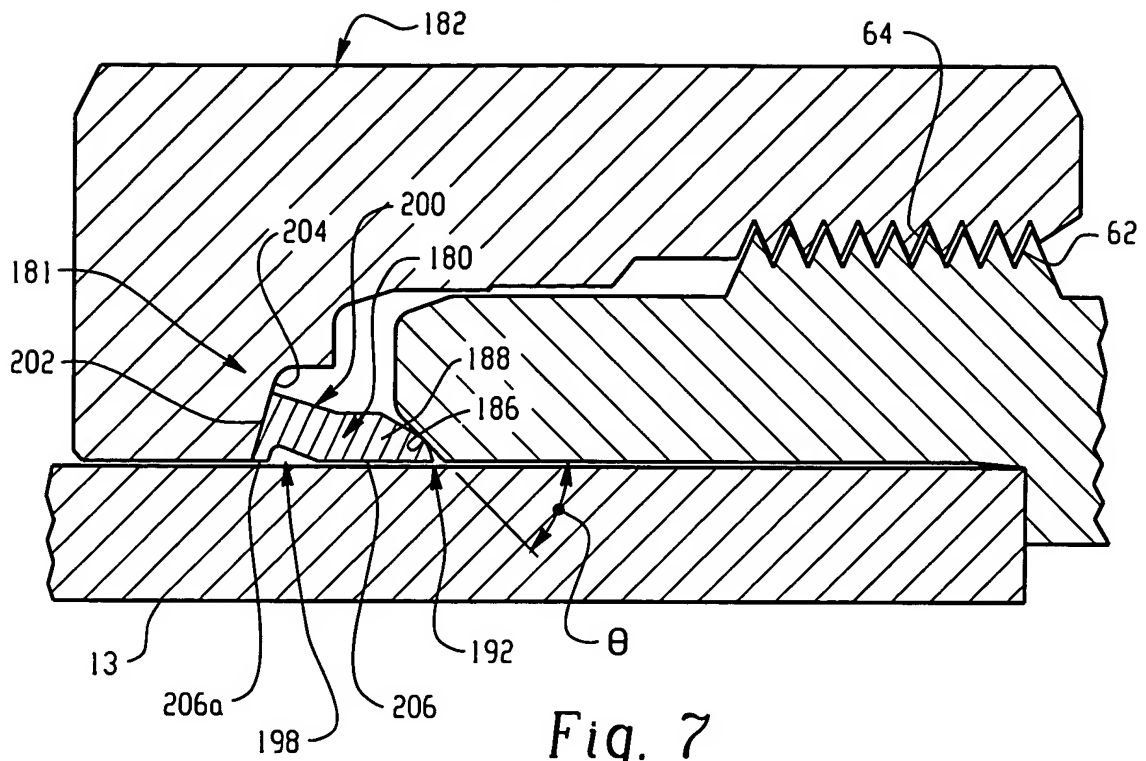


Fig. 6



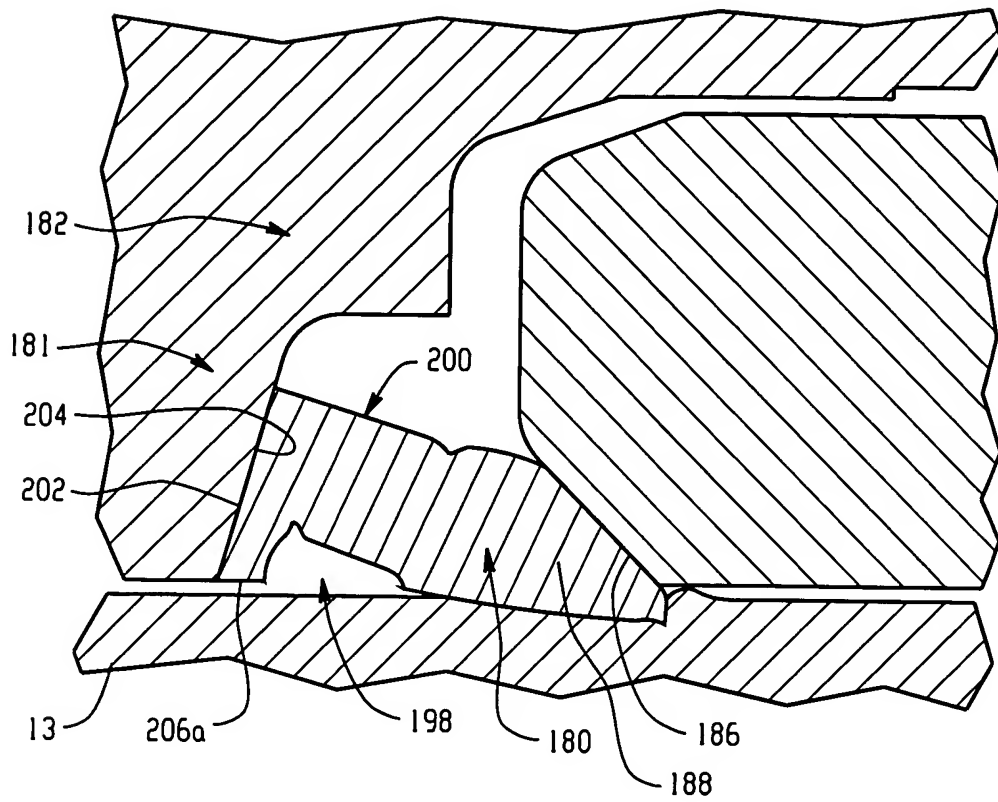


Fig. 8

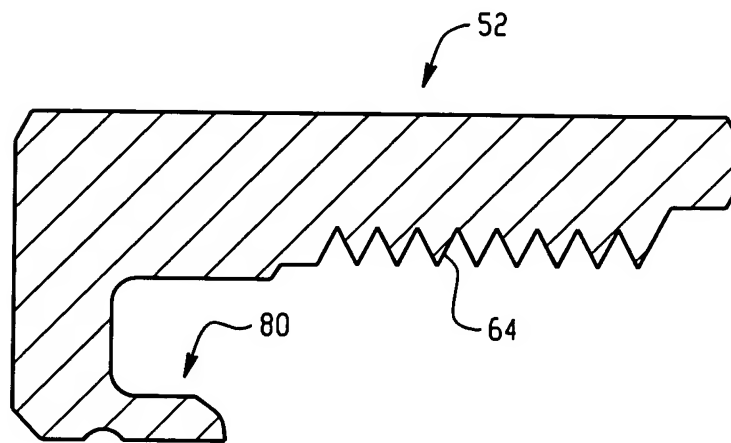


Fig. 9

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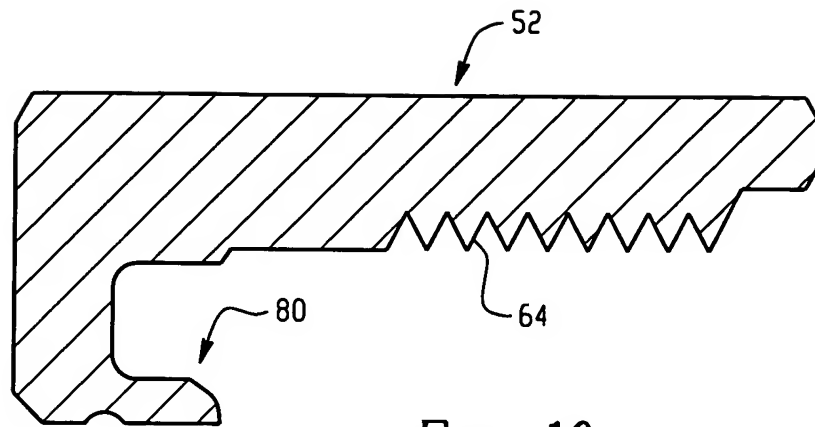


Fig. 10

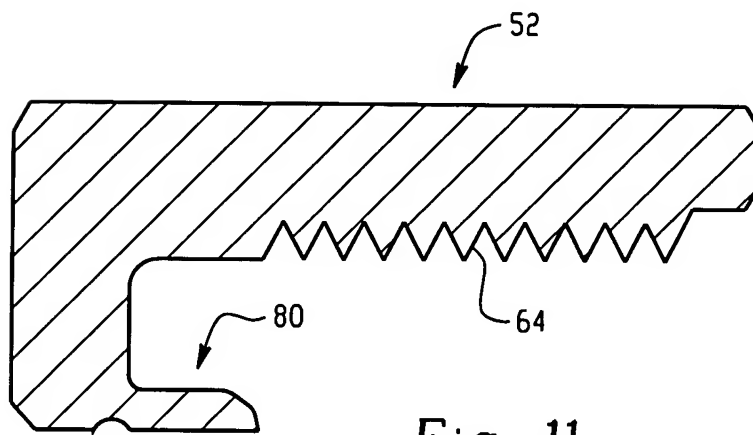


Fig. 11

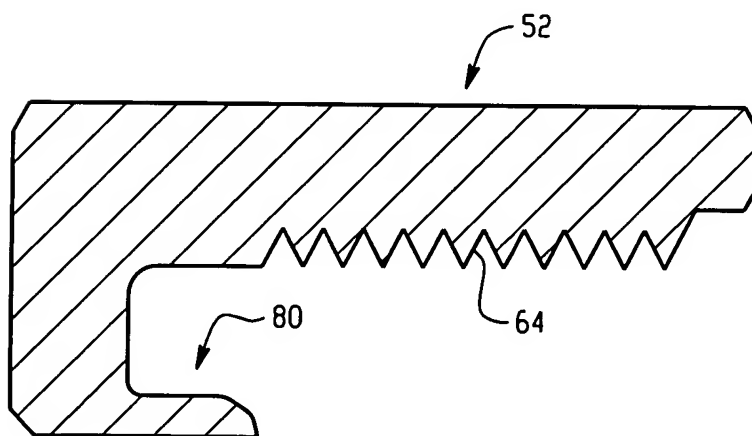


Fig. 12

FIG. 13

FIG. 13 is a cross-sectional view of a semiconductor device. The device includes a substrate 13. A layer 300 is formed on the substrate 13. A layer 306 is formed on top of layer 300. A layer 304 is formed on top of layer 306. A layer 312 is formed on top of layer 306. A layer 320 is formed on top of layer 312. A layer 324 is formed on top of layer 320. A layer 324a is formed on top of layer 324. A layer 324b is formed on top of layer 324a. A layer 306a is formed on top of layer 324. A layer 316 is formed on top of layer 324. A layer 314 is formed on top of layer 316. A layer 313 is formed on top of layer 314. A layer 302 is formed on top of layer 313. A layer 308 is formed on top of layer 302. A layer 310 is formed on top of layer 308. An angle θ is indicated between a horizontal line and a vertical line. A dashed line X is shown at the bottom.

[illegible]

FIG. 14

300

C1

322

C2

310

312

326

308a

314

X

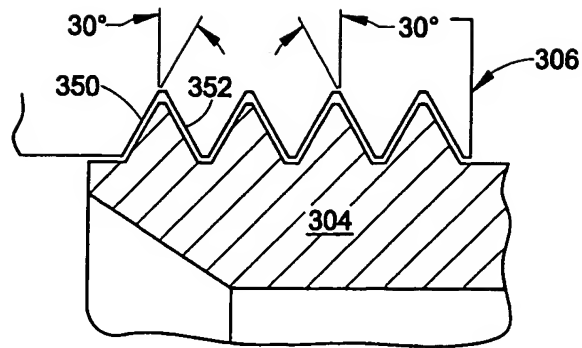


FIG. 15A

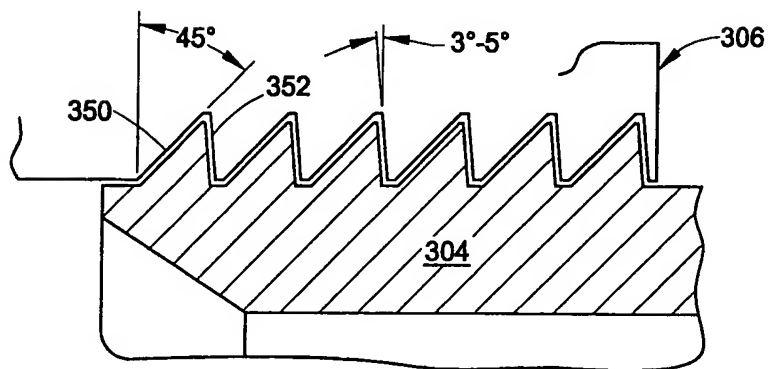


FIG. 15B

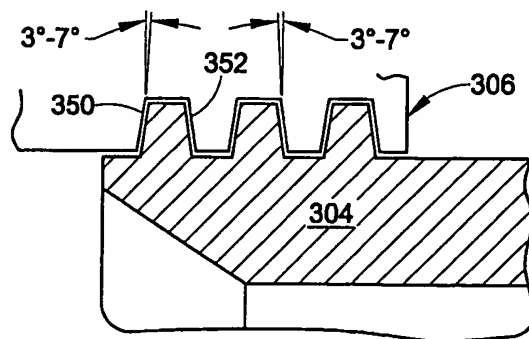


FIG. 15C